

Product Summary

| BV _{SSS} | R _{SS(ON)} Typ | I _S Max T _A = +25°C |
|-------------------|--------------------------------|--|
| 24V | 3.1mΩ @ V _{GS} = 3.8V | 26.5A |

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{SS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

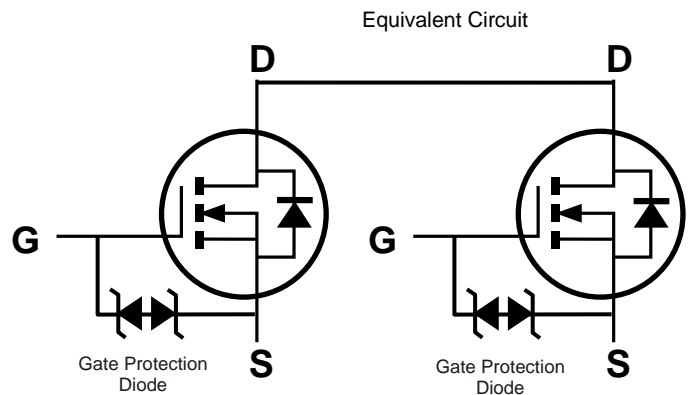
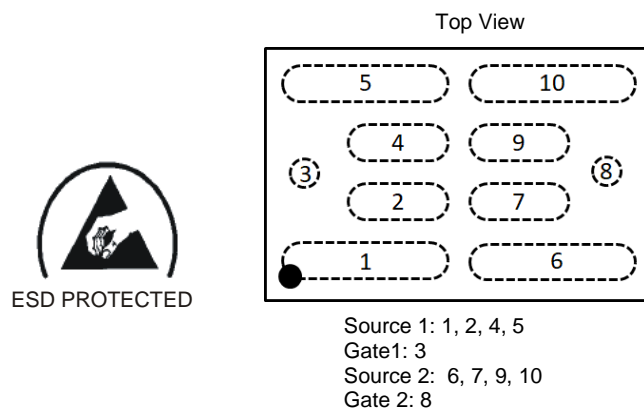
- Battery Management
- Load Switch
- Battery Protection

Features

- CSP with Footprint 3.20mm × 2.10mm
 - Height = 0.120mm (Typical) for Low Profile
 - ESD Protection of Gate
 - Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
 - Halogen and Antimony Free. "Green" Device (Note 3)**
 - For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.
- <https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: X4-DSN3221-10
- Terminal Connections: See Diagram Below
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiAu. Solderable per MIL-STD-202, Method 208 ⁽⁴⁾
- Weight: 0.0016 grams (Approximate)

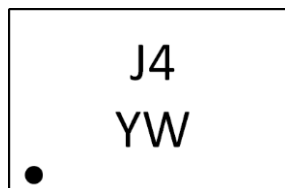


Ordering Information (Note 4)

| Part Number | Package | Packing | |
|----------------|---------------|---------|-------------|
| | | Qty. | Carrier |
| DMN22M5UCA10-7 | X4-DSN3221-10 | 3000 | Tape & Reel |

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



J4 = Product Type Marking Code
YW = Date Code Marking
Y or \bar{Y} = Year (ex: 1 = 2021)
W or \bar{W} = Week (ex: a = Week 27; z Represents Week 52 and 53)

Date Code Key

| Year | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 | 2030 | 2031 | 2032 |
|------|------|------|------|------|------|------|------|------|------|------|------|------|
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | 1 | 2 |

| Week | 1-26 | 27-52 | 53 |
|------|------|-------|----|
| Code | A-Z | a-z | z |

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|---|--------------|------------------------|------------------|-------|------|
| Source-Source Voltage | | | V _{SSS} | 24 | V |
| Gate-Source Voltage | | | V _{GSS} | ±12 | V |
| Continuous Source Current (Note 5) V _{GS} = 4.5V | Steady State | T _A = +25°C | I _S | 26.5 | A |
| | | T _A = +70°C | | 21.5 | |
| Continuous Source Current (Note 5) V _{GS} = 2.5V | Steady State | T _A = +25°C | I _S | 16.5 | A |
| | | T _A = +70°C | | 13.5 | |
| Pulsed Source Current (Note 6) | | | I _{SM} | 110 | A |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|--|-----------------------------------|-------------|------|
| Power Dissipation (Note 7) | P _D | 0.96 | W |
| Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 7) | R _{θJA} | 130 | °C/W |
| Power Dissipation (Note 5) | P _D | 3.14 | W |
| Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5) | R _{θJA} | 39.8 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|--|---------------------|-----|------|-----|------|--|
| OFF CHARACTERISTICS (Note 8) | | | | | | |
| Source-Source Breakdown Voltage | BV _{SSS} | 24 | — | — | V | V _{GS} = 0V, I _S = 1mA |
| Zero Gate Voltage Drain Current T _J = +25°C | I _{SSS} | — | — | 1 | μA | V _{SS} = 19.2V, V _{GS} = 0V |
| Gate-Source Leakage | I _{GSS} | — | — | ±10 | μA | V _{GS} = ±8V, V _{SS} = 0V |
| ON CHARACTERISTICS (Note 8) | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 0.4 | — | 1.3 | V | V _{SS} = 10V, I _S = 1mA |
| Static Source-Source On-Resistance | R _{SS(ON)} | 1.6 | 3.0 | 4.0 | mΩ | V _{GS} = 4.5V, I _S = 5A |
| | | 1.7 | 3.1 | 4.1 | | V _{GS} = 3.8V, I _S = 5A |
| | | 2.0 | 3.4 | 4.7 | | V _{GS} = 3.1V, I _S = 5A |
| | | 2.2 | 3.8 | 7.4 | | V _{GS} = 2.5V, I _S = 5A |
| Diode Forward Voltage | V _{SS} | — | — | 1.2 | V | V _{GS} = 0V, I _S = 3A |
| DYNAMIC CHARACTERISTICS (Note 9) | | | | | | |
| Input Capacitance | C _{ISS} | — | 3490 | — | pF | V _{SS} = 12V, V _{GS} = 0V, f = 1.0kHz |
| Output Capacitance | C _{OSS} | — | 400 | — | | |
| Reverse Transfer Capacitance | C _{RSS} | — | 220 | — | | |
| Gate Resistance | R _G | — | 281 | — | Ω | V _{GS} = 0V, V _{DS} = 0V, f = 1MHz |
| Total Gate Charge | Q _G | — | 40.7 | — | nC | V _{DD} = 12V, V _{GS} = 4.5V, I _S = 5A |
| Gate-Source Charge | Q _{GS} | — | 6.9 | — | | |
| Gate-Drain Charge | Q _{GD} | — | 10.5 | — | | |
| Gate Charge at V _{TH} | Q _{G(TH)} | — | 3.5 | — | | |
| Turn-On Delay Time | t _{D(ON)} | — | 326 | — | ns | V _{DD} = 12V, V _{GS} = 4.5V, I _S = 5A |
| Turn-On Rise Time | t _R | — | 869 | — | | |
| Turn-Off Delay Time | t _{D(OFF)} | — | 2664 | — | | |
| Turn-Off Fall Time | t _F | — | 2580 | — | | |

- Notes:
- Device mounted on FR-4 material with 1inch² (6.45cm²), 2oz. (0.071mm thick) Cu.
 - Repetitive rating, pulse width limited by junction temperature.
 - Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

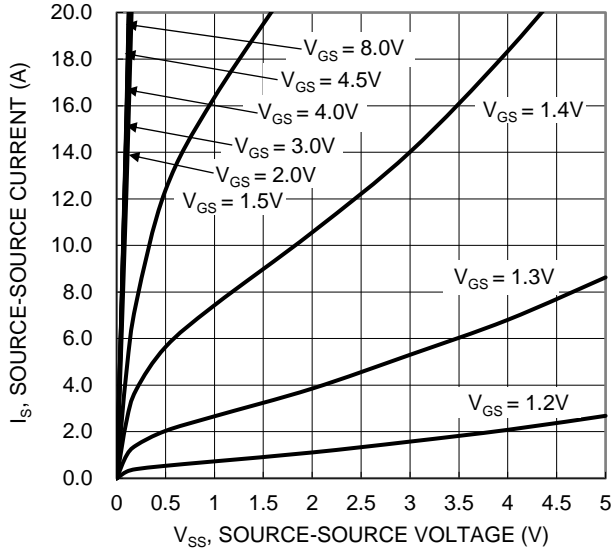


Figure 1. Typical Output Characteristic

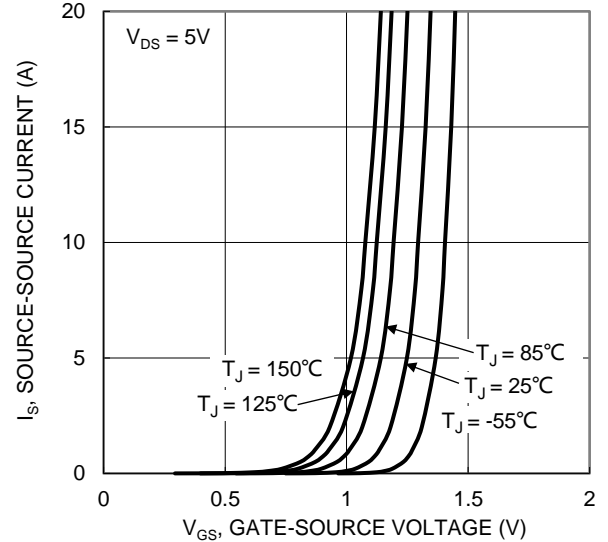


Figure 2. Typical Transfer Characteristic

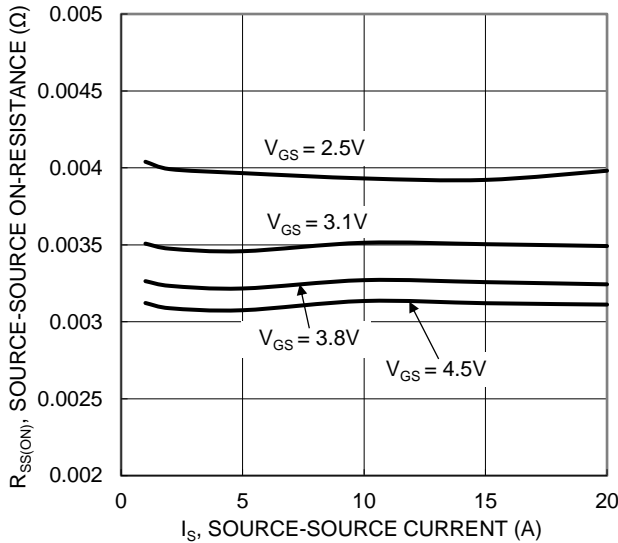


Figure 3. Typical On-Resistance vs. Source Current and Gate Voltage

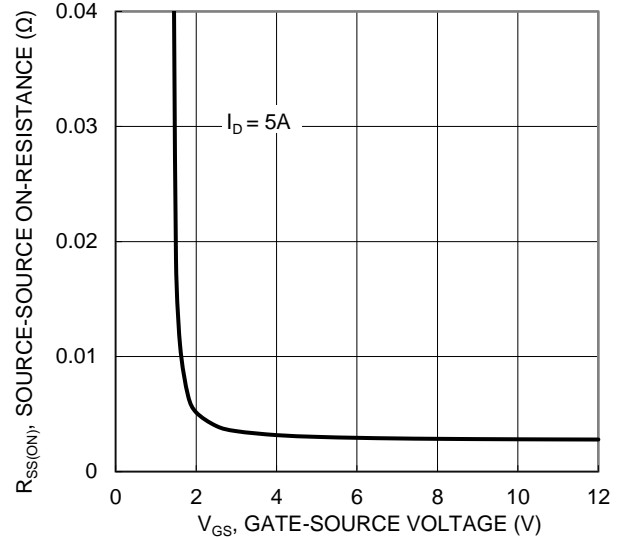


Figure 4. Typical Transfer Characteristic

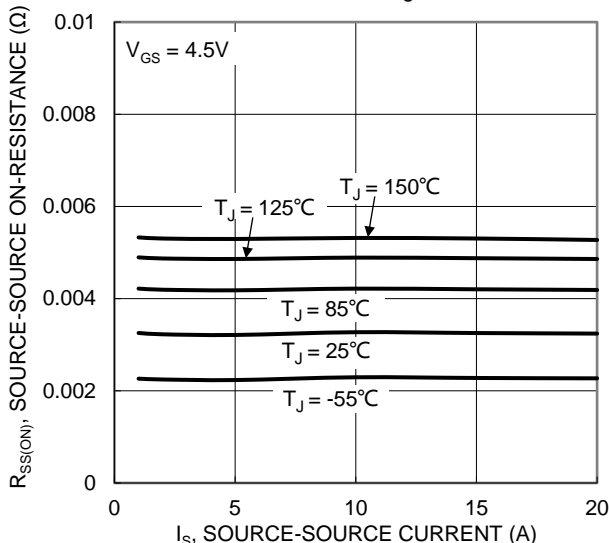


Figure 5. Typical On-Resistance vs. Source Current and Junction Temperature

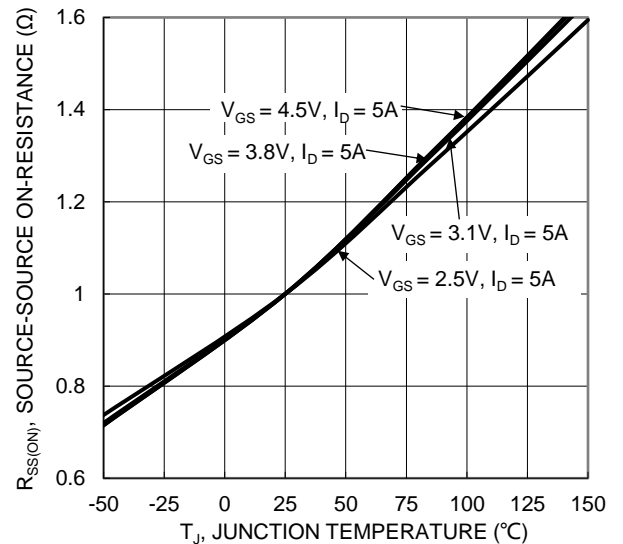


Figure 6. On-Resistance Variation with Junction Temperature

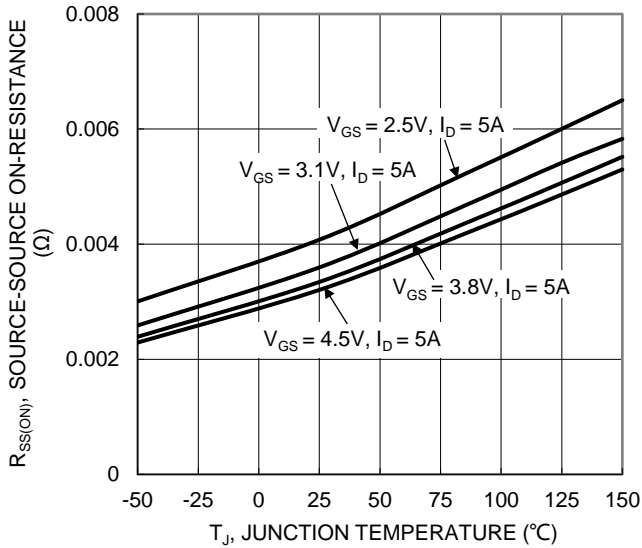


Figure 7. On-Resistance Variation with Junction Temperature

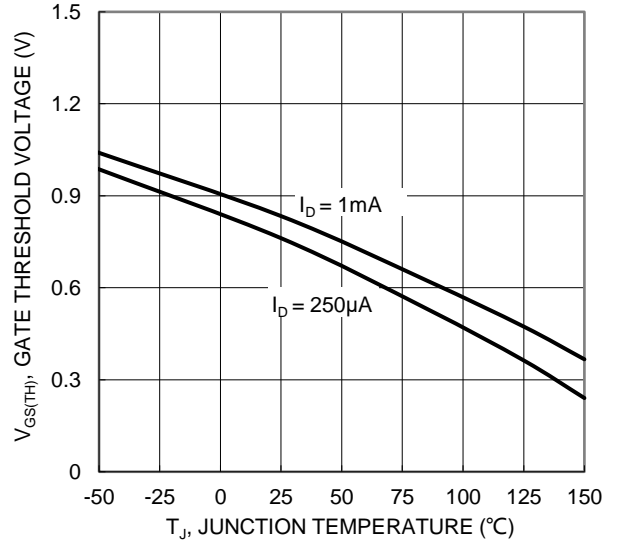


Figure 8. Gate Threshold Variation vs. Junction Temperature

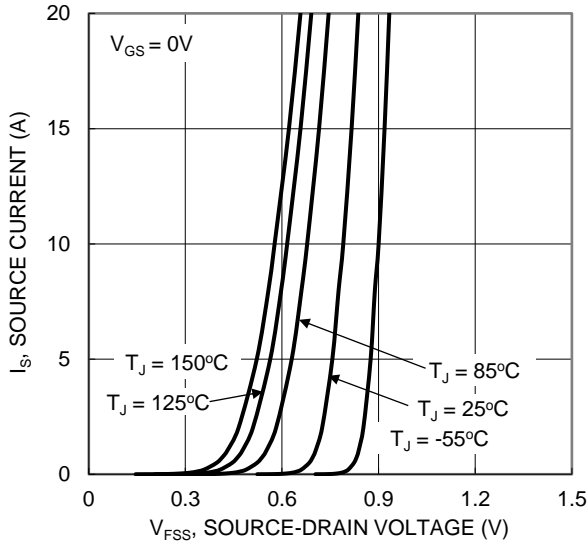


Figure 9. Diode Forward Voltage vs. Current

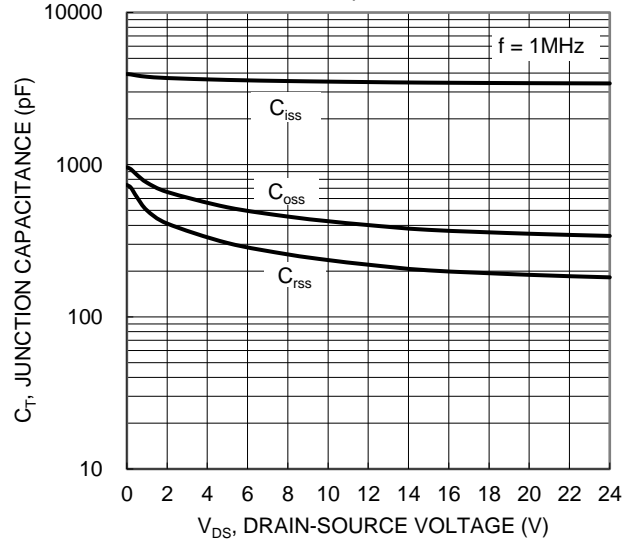


Figure 10. Typical Junction Capacitance

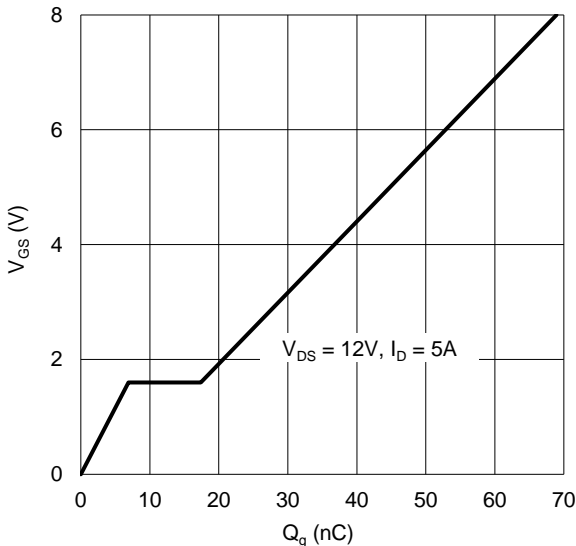


Figure 11. Gate Charge

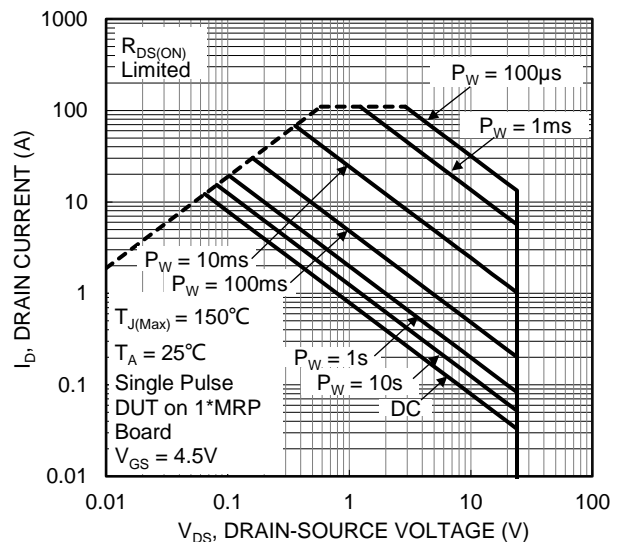


Figure 12. SOA, Safe Operation Area

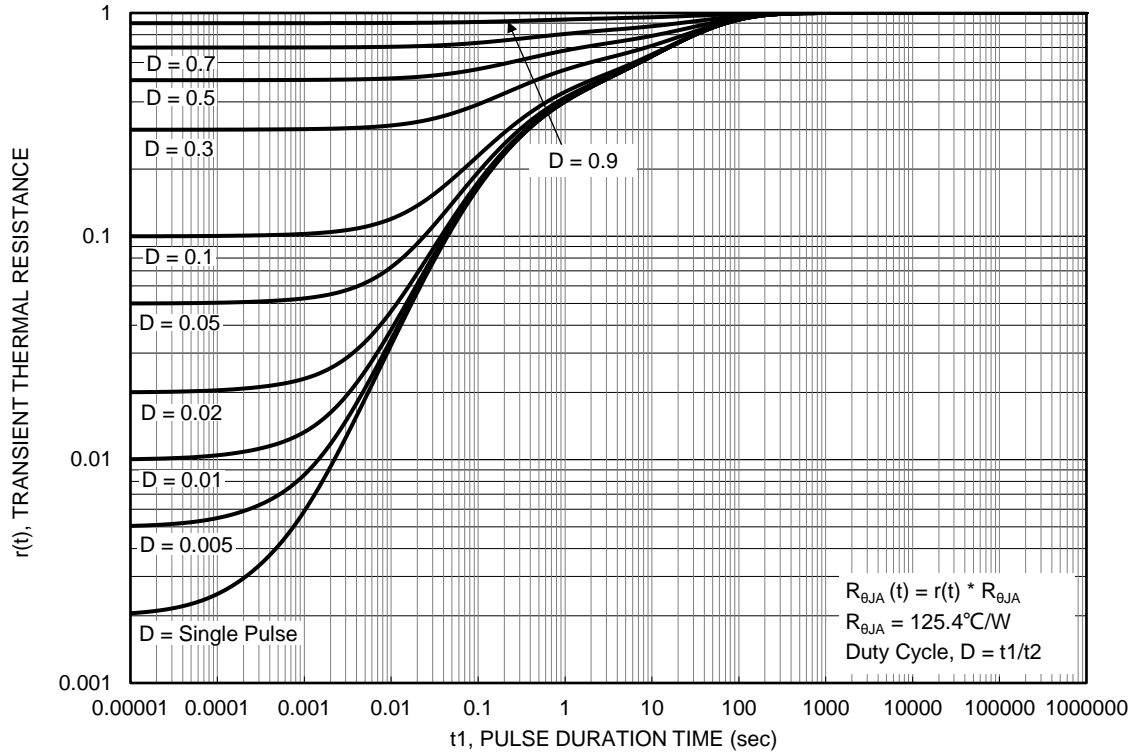
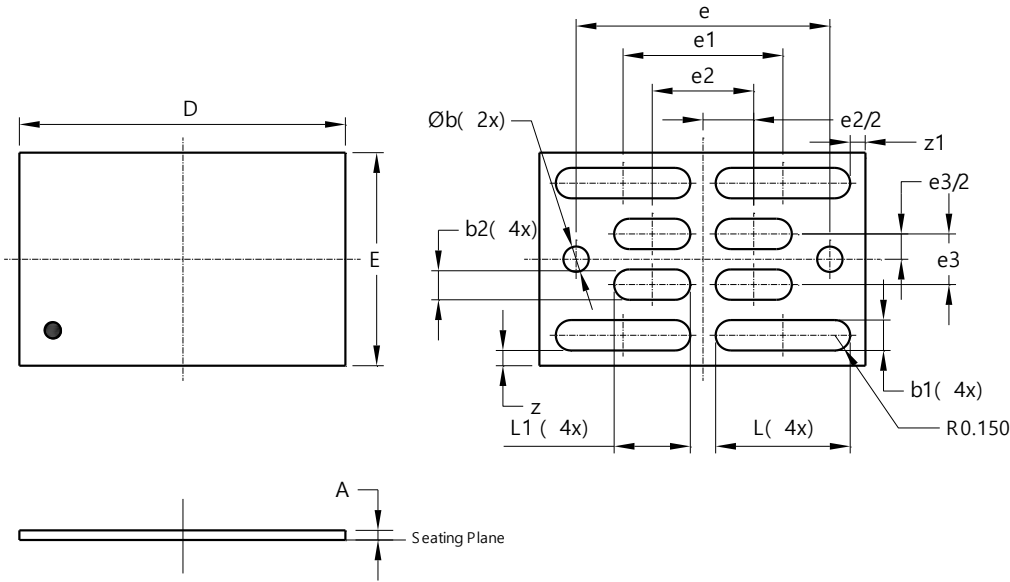


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X4-DSN3221-10

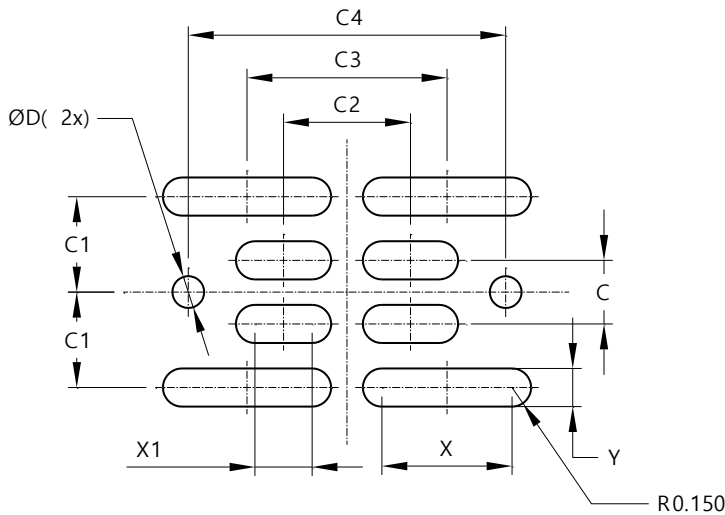


| X4-DSN3221-10 | | | |
|-----------------------------|-----------|-------|-------|
| Dim | Min | Max | Typ |
| A | -- | 0.150 | 0.120 |
| b | 0.220 | 0.280 | 0.250 |
| b1 | 0.270 | 0.330 | 0.300 |
| b2 | 0.270 | 0.330 | 0.300 |
| D | 3.170 | 3.230 | 3.200 |
| E | 2.070 | 2.130 | 2.100 |
| e | 2.500 BSC | | |
| e1 | 1.575 BSC | | |
| e2 | 1.000 BSC | | |
| e3 | 0.500 BSC | | |
| L | 1.295 | 1.355 | 1.325 |
| L1 | 0.720 | 0.780 | 0.750 |
| z | 0.120 | 0.180 | 0.150 |
| z1 | 0.120 | 0.170 | 0.150 |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X4-DSN3221-10



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 0.500 |
| C1 | 0.750 |
| C2 | 1.000 |
| C3 | 1.575 |
| C4 | 2.500 |
| D | 0.250 |
| X | 1.025 |
| X1 | 0.450 |
| Y | 0.300 |

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